

## Group IV superconductor-semiconductor epitaxy for integrated quantum electronics

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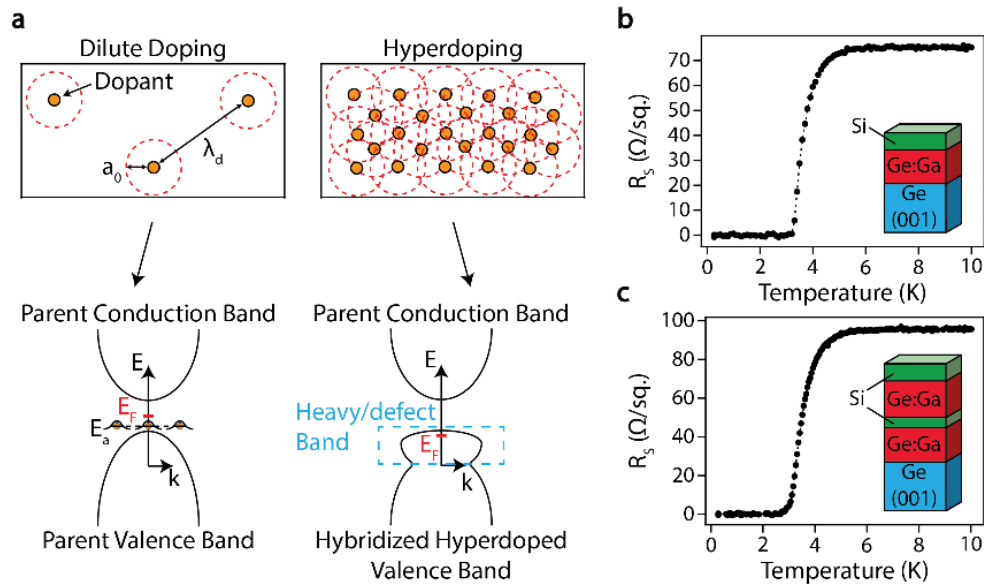


Figure 1: **a.** Schematic of dopant structure and resulting schematic band structure at zone center for dilute doping and hyperdoping scenarios. **b.** Sheet resistance versus temperature plot for a single layer film of gallium-doped germanium. **c.** Sheet resistance versus temperature plot for a double-layer gallium-doped germanium heterostructure.